

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination	
		10/612,941	YOON, DONG-SOO	
		Examiner	Art Unit	Page 1 of 1
		Lisa A Kilday	2829	

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	K	US-			
	L	US-			
	M	US-			

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
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